



VOIDLESS-HERMETICALLY SEALED FAST RECOVERY GLASS RECTIFIERS

Qualified per MIL-PRF-19500/424

*Qualified Levels:
JAN, JANTX
and JANTXV*

DESCRIPTION

This “fast recovery” rectifier diode series is military qualified and is ideal for high-reliability applications where a failure cannot be tolerated. These industry-recognized 3.0 amp rated rectifiers for working peak reverse voltages from 100 to 600 volts are hermetically sealed with voidless-glass construction using an internal “Category I” metallurgical bond. Microsemi also offers numerous other rectifier products to meet higher and lower current ratings with various recovery time speed requirements including fast and ultrafast device types in both through-hole and surface mount packages.

Important: For the latest information, visit our website <http://www.microsemi.com>.

FEATURES

- JEDEC registered 1N5186 thru 1N5190 series.
- Voidless hermetically sealed glass package.
- Working Peak Reverse Voltage 100 to 600 volts.
- Internal “Category I” metallurgical bond.
- JAN, JANTX, and JANTXV qualifications are available per MIL-PRF-19500/424.
- RoHS compliant versions available (commercial grade only).

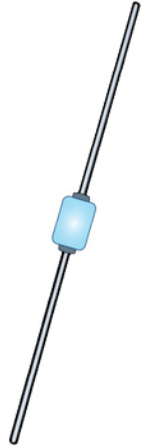
APPLICATIONS / BENEFITS

- Fast recovery 3 amp 100 to 600 volt rectifiers.
- Military and other high-reliability applications.
- General rectifier applications including bridges, half-bridges, catch diodes, etc.
- High forward surge current capability.
- Extremely robust construction.
- Low thermal resistance.
- Controlled avalanche with peak reverse power capability.
- Inherently radiation hard as described in Microsemi “[MicroNote 050](#)”.

MAXIMUM RATINGS

Parameters/Test Conditions	Symbol	Value	Unit	
Junction and Storage Temperature	T _J and T _{STG}	-65 to +175	°C	
Thermal Resistance Junction-to-Lead ⁽¹⁾	R _{θJL}	20	°C/W	
Forward Surge Current @ 8.3 ms half-sine, T _A = +150 °C	I _{FSM}	80	A	
Working Peak Reverse Voltage	V _{RWM}	1N5186	100	V
		1N5187	200	
		1N5188	400	
		1N5190	600	
Average Rectified Forward Current	I _O	@ T _A = +25 °C	3.0	A
		@ T _A = +150 °C	0.700	
Maximum Reverse Recovery Time	t _{rr}	1N5186	150	ns
		1N5187	200	
		1N5188	250	
		1N5190	400	
Solder Temperature @ 10 s	T _{SP}	260	°C	

Notes: 1. At 3/8 inch (10 mm) lead length from body.



“B” Package

MSC – Lawrence

6 Lake Street,
Lawrence, MA 01841
1-800-446-1158
Tel: (978) 620-2600
Fax: (978) 689-0803

MSC – Ireland

Gort Road Business Park,
Ennis, Co. Clare, Ireland
Tel: +353 (0) 65 6840044
Fax: +353 (0) 65 6822298

Website:

www.microsemi.com

MECHANICAL and PACKAGING

- CASE: Hermetically sealed voidless hard glass with tungsten slugs.
- TERMINALS: Tin/lead (Sn/Pb) over nickel (Ni) coat or RoHS compliant matte-tin (commercial grade only) over copper.
- MARKING: Body is coated and marked with part number.
- POLARITY: Cathode band.
- TAPE & REEL option: Standard per EIA-296. Consult factory for quantities.
- WEIGHT: 797 milligrams.
- See [Package Dimensions](#) on last page.

PART NOMENCLATURE

JAN 1N5186 e3

Reliability Level

JAN = JAN Level
 JANTX = JANTX Level
 JANTXV = JANTXV Level
 Blank = Commercial

RoHS Compliance

e3 = RoHS compliant (available on commercial grade only)
 Blank = non-RoHS compliant

JEDEC type number

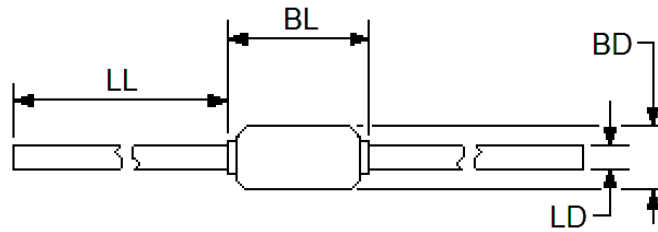
See [Electrical Characteristics](#) table

SYMBOLS & DEFINITIONS

Symbol	Definition
$V_{(BR)}$	Minimum Breakdown Voltage: The minimum voltage the device will exhibit at a specified current.
V_{RWM}	Working Peak Reverse Voltage: The maximum peak voltage that can be applied over the operating temperature range.
V_F	Maximum Forward Voltage: The maximum forward voltage the device will exhibit at a specified current.
I_R	Maximum Leakage Current: The maximum leakage current that will flow at the specified voltage and temperature.
t_{rr}	Reverse Recovery Time: The time interval between the instant the current passes through zero when changing from the forward direction to the reverse direction and a specified decay point after a peak reverse current occurs.

ELECTRICAL CHARACTERISTICS

TYPE	MINIMUM BREAKDOWN VOLTAGE	FORWARD VOLTAGE		MAXIMUM REVERSE CURRENT	
	$V_{(BR)}$ @ 100 μ A	V_F @ 9 A (pulsed)		I_R @ V_{RWM}	
	Volts	MIN Volts	MAX Volts	25 °C μ A	100 °C μ A
1N5186	120	0.9	1.5	2.0	100
1N5187	240	0.9	1.5	2.0	100
1N5188	480	0.9	1.5	2.0	100
1N5190	660	0.9	1.5	2.0	100

PACKAGE DIMENSIONS


Symbol	Dimension				Notes
	Inch		Millimeters		
	Min	Max	Min	Max	
BD	0.115	0.155	2.92	3.94	3
LD	0.038	0.042	0.97	1.07	
BL	0.150	0.300	3.81	7.62	4
LL	1.00	1.50	25.40	38.10	

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Dimension BD shall be measured at the largest diameter. The BL dimension shall include the entire body including slugs.
4. Dimension BL shall include the sections of the lead over which the diameter is uncontrolled.
This uncontrolled area is defined as the zone between the edge of the diode body and extending .050 inch (1.27 mm) onto the leads.
5. In accordance with ASME Y14.5M, diameters are equivalent to Φ x symbology.

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Microchip:

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